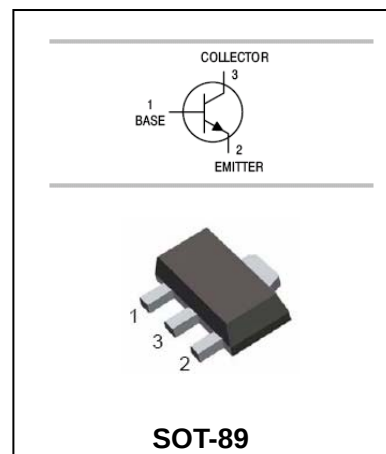


NPN Silicon Epitaxial Planar Transistor

2SC2884

FEATURES

- Suitable for output stage of 1 watts amplifier.
- High DC current gain.
- Small flat package.
- $P_C=1.0$ to $2.0W$.
- Complements the 2SA1204.



ORDERING INFORMATION

Type No.	Marking	Package Code
2SC2884	PO1/PY1	SOT-89

MAXIMUM RATING @ $T_a=25^{\circ}C$ unless otherwise specified

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	35	V
V_{CEO}	Collector-Emitter Voltage	30	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	0.8	A
I_B	Base Current	0.16	A
P_C	Collector Dissipation	500	mW
T_j, T_{stg}	Junction and Storage Temperature	-55 to +150	$^{\circ}C$



NPN Silicon Epitaxial Planar Transistor

2SC2884

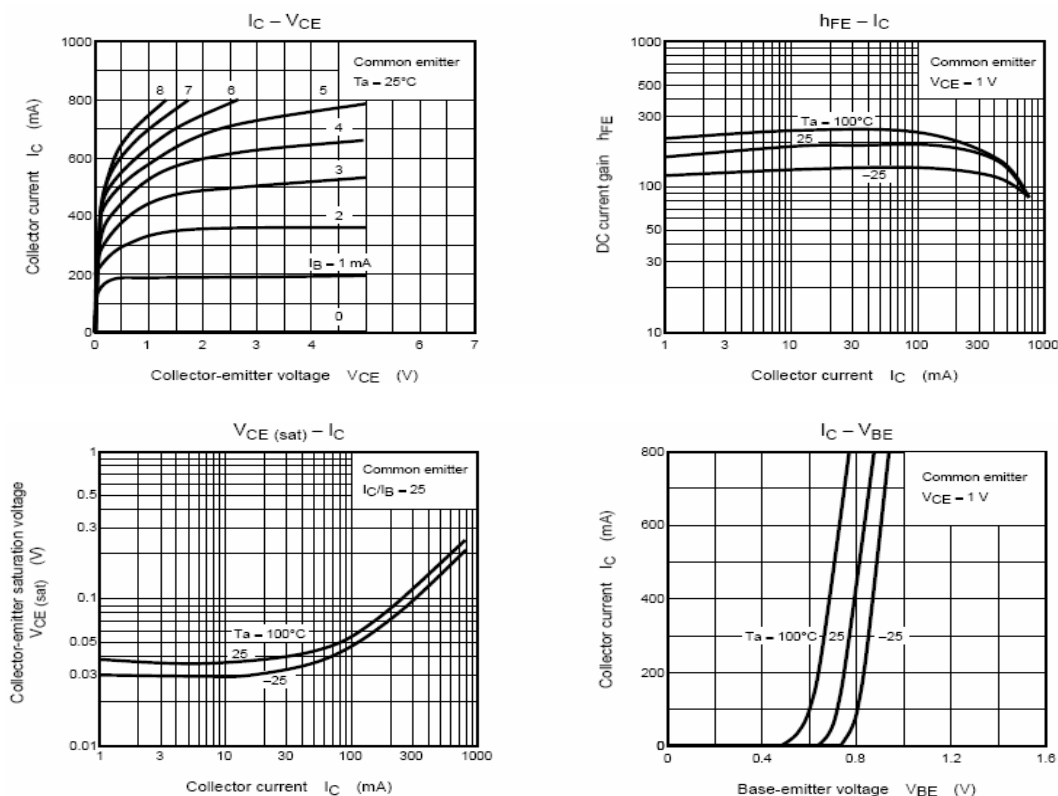
ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10mA, I_B=0$	30			V
Collector cut-off current	I_{CBO}	$V_{CB}=35V, I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5V, I_C=0$			0.1	μA
DC current gain	h_{FE}	$V_{CE}=1V, I_C=100mA$	100		320	
		$V_{CE}=1V, I_C=700mA$	35			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=0.5A, I_B=0.02A$			0.5	V
Base-emitter voltage	V_{BE}	$V_{CE}=1V, I_C=10mA$	0.5		0.8	V
Transition frequency	f_T	$V_{CE}=5V, I_C=10mA$		120		MHz
Collector output capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=1MHz$		13		pF

CLASSIFICATION OF h_{FE}

Rank	O	Y
Range	100-200	160-320
MARKING	PO1	PY1

TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified



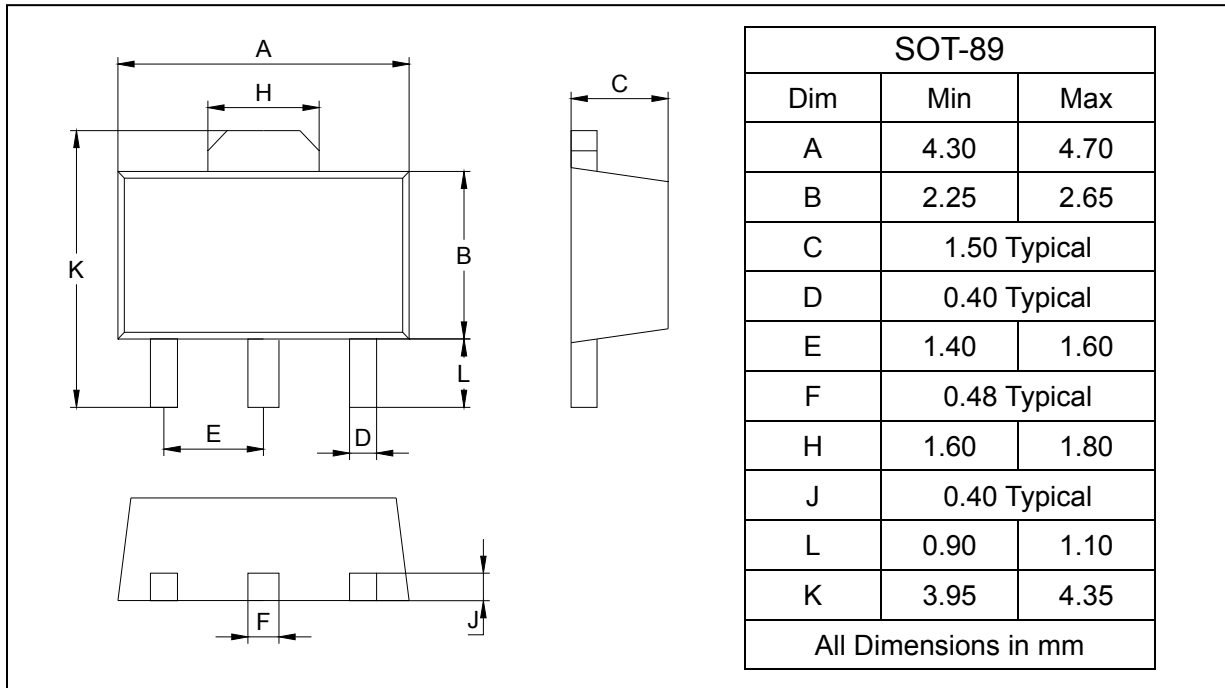
NPN Silicon Epitaxial Planar Transistor

2SC2884

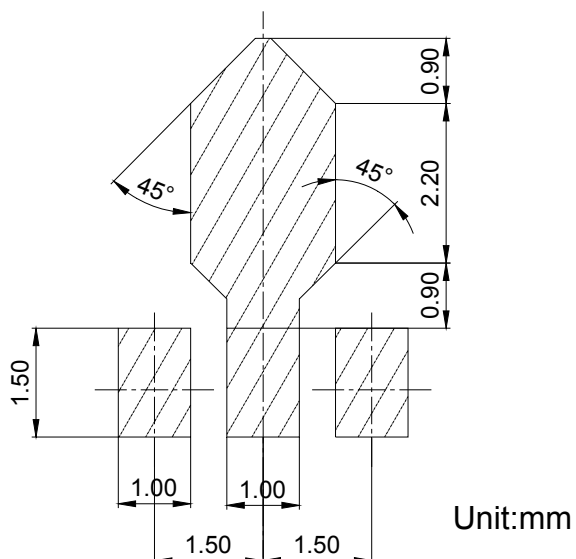
PACKAGE OUTLINE

Plastic surface mounted package

SOT-89



SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
2SC2884	SOT-89	1000/Tape&Reel